

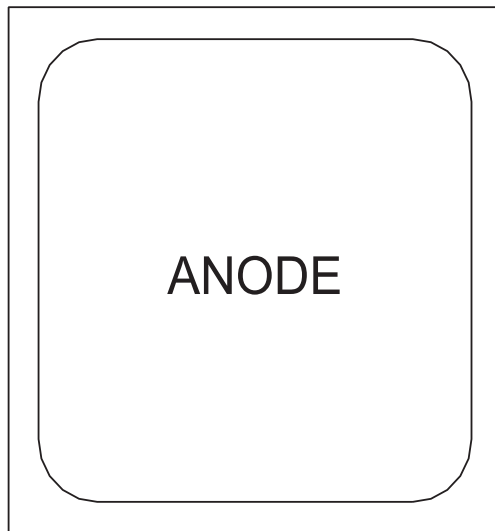
PROCESS CPD18
Ultra Fast Rectifier
8 Amp Glass Passivated Rectifier Chip



PROCESS DETAILS

| | |
|------------------------|-----------------------|
| Process | GLASS PASSIVATED MESA |
| Die Size | 100 x 100 MILS |
| Die Thickness | 14 MILS |
| Anode Bonding Pad Area | 78 x 78 MILS |
| Top Side Metalization | Ni/Au - 5,000Å/2,000Å |
| Back Side Metalization | Ni/Au - 5,000Å/2,000Å |

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,170

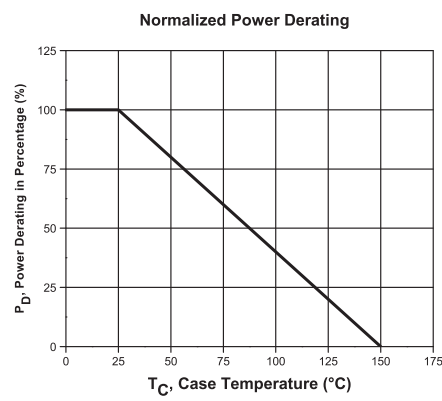
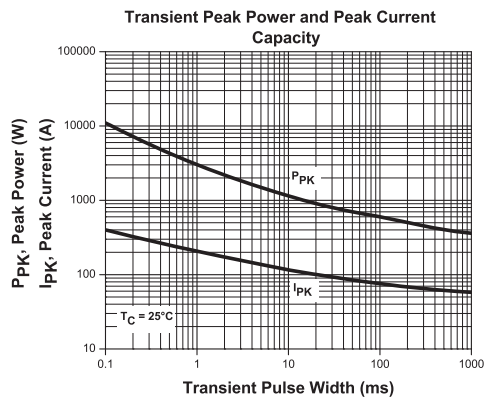
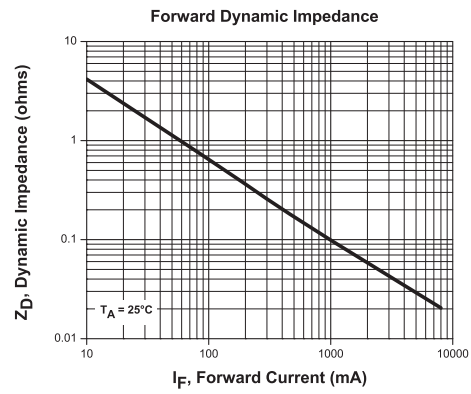
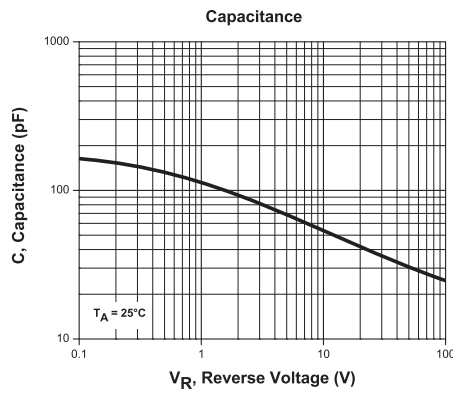
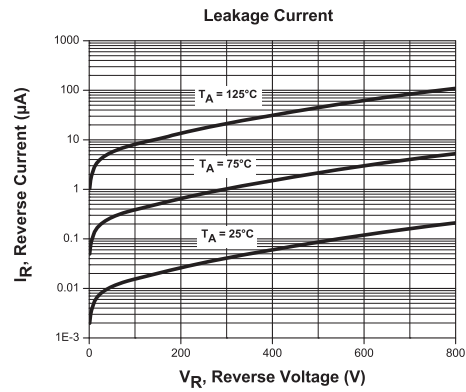
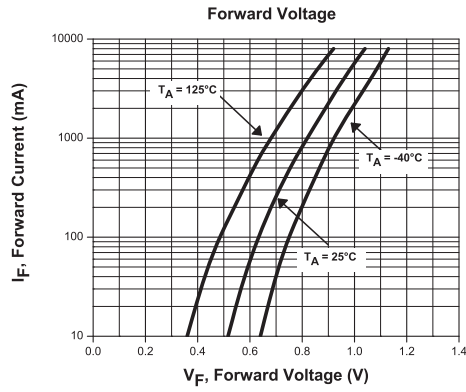
PRINCIPAL DEVICE TYPES

1N5807 thru 1N5811
UES1301 thru UES1306
UES1401 thru UES1403
CUDD8-02 Series

R4 (22-March 2010)

PROCESS CPD18

Typical Electrical Characteristics



R4 (22-March 2010)